# **DSA2401**

### Silicon PNP epitaxial planar type

#### For low frequency amplification

#### Features

- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

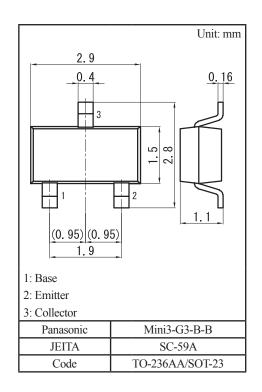
#### Marking Symbol: B1

#### Packaging

DSA2401×0L Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-15	V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-10	V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	-7	V
Collector current	I <sub>C</sub>	- 0.5	А
Peak collector current	I <sub>CP</sub>	-1	А
Collector power dissipation	P <sub>C</sub>	200	mW
Junction temperature	Tj	150	°C
Operating ambient temperature	T <sub>opr</sub>	-40 to +85	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C



#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

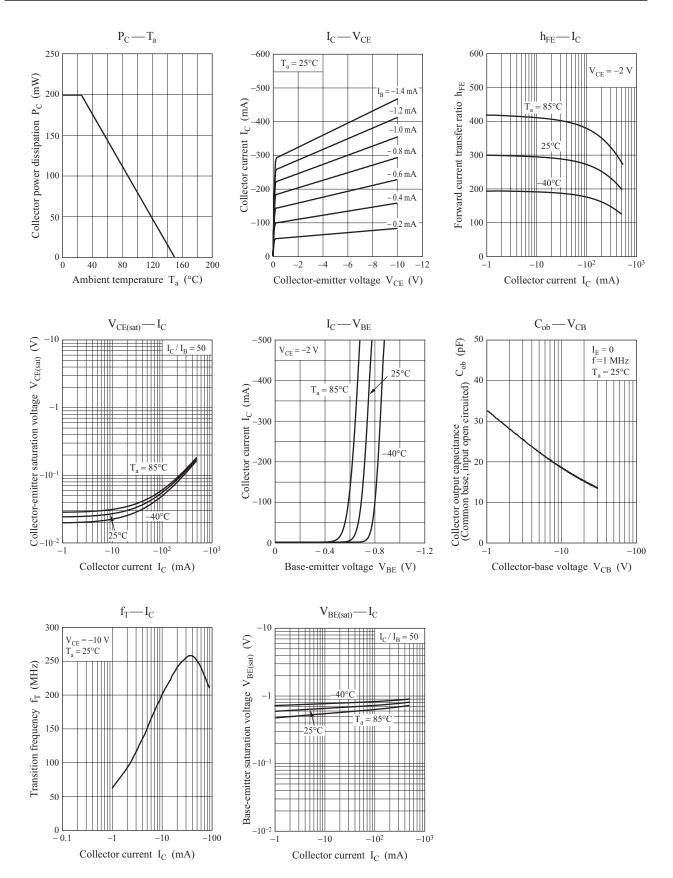
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = -10 \ \mu {\rm A}, I_{\rm E} = 0$	-15			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -1  {\rm mA}, I_{\rm B} = 0$	-10			V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_{\rm E} = -10 \ \mu {\rm A}, I_{\rm C} = 0$	-7			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -10 \text{ V}, I_E = 0$			-100	nA
Forward current transfer ratio *1	h <sub>FE1</sub> *2	$V_{CE} = -2 V, I_C = -0.5 A$	130		350	
	h <sub>FE2</sub>	$V_{CE} = -2 V, I_C = -1 A$	60			
Collector-emitter saturation voltage *1	V <sub>CE(sat)</sub>	$I_{\rm C} = -0.4  \text{A}, I_{\rm B} = -8  \text{mA}$		-0.15	-0.30	V
Base-emitter saturation voltage *1	V <sub>BE(sat)</sub>	$I_{\rm C} = -0.4 \rm{A},  I_{\rm B} = -8 \rm{mA}$		- 0.8	-1.2	V
Transition frequency	f <sub>T</sub>	$V_{CE} = -10 \text{ V}, I_C = -50 \text{ mA}$		250		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		18		pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*1: Pulse measurement

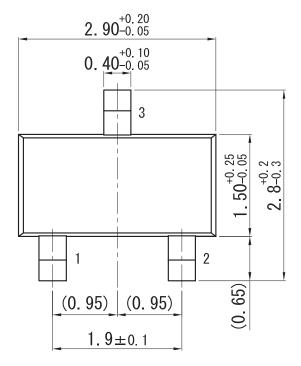
\*2: Rank classification

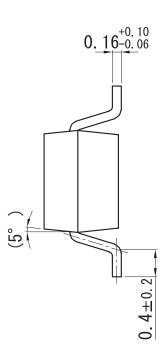
Code	R	S
Rank	R	S
$h_{\rm FE1}$	130 to 220	180 to 350
Marking Symbol	B1R	B1S

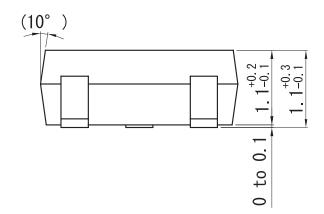


Unit: mm

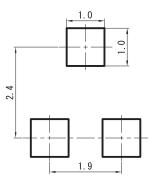
# Mini3-G3-B-B







Land Pattern (Reference) (Unit: mm)



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